

File Number 34

2N1893, 2N2405

## Medium-Power Silicon N-P-N Planar Transistors

For Small-Signal Applications  
In Industrial and Commercial Equipment

**Features:**

- For operation at junction temperature up to 200°C
- Planar construction for low noise and low leakage
- Low output capacitance

The RCA-2N1893 and 2N2405\* are silicon n-p-n planar transistors intended for a variety of small-signal and medium-power applications. They feature exceptionally high collector-to-emitter sustaining voltage, low leakage characteristics, high switching speeds, and high pulse beta ( $h_{FE}$ ).

RCA-2N2405 is a direct replacement for type 2N1893 for most applications. In addition, the 2N2405 has high voltage ratings, lower saturation voltages, and higher sustaining voltages than the 2N1893.

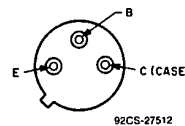
The 2N1893 and 2N2405 are supplied in the TO-205AD package.

\*Formerly Dev. Type TA2235A.

**2N2405 Features:**

- Minimum gain-bandwidth product ( $f_T$ ) of 120 MHz; useful in application from dc to 50 MHz
- High sustaining voltage:  
 $V_{CEO(sus)} = 90$  V min.
- Low saturation voltages:  
 $V_{CE(sat)} = 0.5$  V max. at  $I_C = 150$  mA  
 $V_{BE(sat)} = 1.1$  V max. at  $I_C = 150$  mA

TERMINAL DESIGNATIONS



JEDEC TO-205AD

**MAXIMUM RATINGS, Absolute-Maximum Values:**

	2N1893	2N2405	
* COLLECTOR-TO-BASE VOLTAGE..... $V_{CBO}$	120	120	V
* COLLECTOR-TO-EMITTER SUSTAINING VOLTAGE: With external base-to-emitter resistance ( $R_{BE}$ ) $\leq 10 \Omega$ ..... $V_{CER}$	100	140	V
With base open..... $V_{CEO}$	80	90	V
* EMITTER-TO-BASE VOLTAGE..... $V_{EBO}$	7	7	V
* COLLECTOR CURRENT..... $I_C$	0.5	1	A
* TRANSISTOR DISSIPATION: At case temperature up to 25°C..... $P_T$	3	5	W
At free-air temperatures up to 25°C.....	0.8	1	W
At temperatures above 25°C.....	See Figs 1 & 2		
* TEMPERATURE RANGE: Storage and operating (Junction)..... $T_{stg}, T_J$	-65 to +200		°C
* LEAD TEMPERATURE (During soldering): At distance from seating plane for 10 s max. $\geq 1/16$ in. (1.58 mm) for 2N1893 and $\geq 1/32$ in. (0.8 mm) for 2N2405..... $T_L$	255		°C

\* In accordance with JEDEC registration data format (JS-9 RDF-2).

**2N1893, 2N2405**

ELECTRICAL CHARACTERISTICS, Case Temperature ( $T_C$ ) = 25°C Unless Otherwise Specified

CHARACTERISTIC	TEST CONDITIONS					LIMITS				UNITS
	VOLTAGE V dc		CURRENT mA dc			2N1893		2N2405		
	$V_{CB}$	$V_{CE}$	$I_C$	$I_E$	$I_B$	Min.	Max.	Min.	Max.	
* $I_{CBO}$ $T_C = 150^\circ C$	90			0		-	0.01	-	0.01	$\mu A$
* $I_{EBO}$ $V_{BE} = -5 V$			0			-	0.01	-	0.01	$\mu A$
* $V_{CEO(sus)}$			100 <sup>a</sup> 30 <sup>a</sup>		0	-	-	90	-	V
* $V_{CER(sus)}$ $R_{BE} = 10 \Omega$ $R_{BE} = 500 \Omega$			100 <sup>a</sup> 100 <sup>a</sup>			100	-	140	-	V
* $V_{(BR)CBO}$			0.1	0		120	-	120	-	V
* $V_{(BR)EBO}$			0	0.1		7	-	7	-	V
* $V_{CE(sat)}$			150 <sup>a</sup> 50 <sup>a</sup>		15	-	5	-	0.5	V
* $V_{BE(sat)}$			150 <sup>a</sup> 50 <sup>a</sup>		15	-	1.3	-	1.1	V
* $h_{FE}$		10	10	150 <sup>a</sup> 10 <sup>a</sup> 10		40	120	60	200	
* $T_C = 55^\circ C$		10	10			20	-	20	-	
* $h_{fe}$ f = 1 kHz		5	1			30	100	-	-	
* 1 kHz		5	5			-	-	50	275	
* 1 kHz		10	5			45	-	-	-	
* 20 MHz		10	50			2.5	-	6	-	
* $h_{ib}$ f = 1 kHz	5 10		1 5			20 4	30 8	24 4	34 8	$\Omega$
* $h_{rb}$ f = 1 kHz	5 10		1 5			-	$1.25 \times 10^{-4}$ $1.5 \times 10^{-4}$	-	$3 \times 10^{-4}$ $3 \times 10^{-4}$	
* $h_{ob}$ f = 1 kHz	5 10		1 5			-	0.5 0.5	-	0.5 0.5	$\mu mho$
* $C_{obo}$	10			0		-	15	-	15	pF
* $C_{ib}$ $V_{BE} = -0.5 V$				0		-	85	-	80	pF
* NF RG = 500 $\Omega$ BW = 15 kHz f = 1 kHz	10		0.3			-	-	-	6	dB
* $R_{\theta J-C}$						-	58.3	-	35	$^\circ C/W$
* $R_{\theta J-A}$						-	219	-	175	

<sup>a</sup> Pulsed. Pulse duration = 300  $\mu sec$  max.; duty factor  $\leq 2\%$ .  
\* In accordance with JEDEC registration data format (JS-9 RDF-2).

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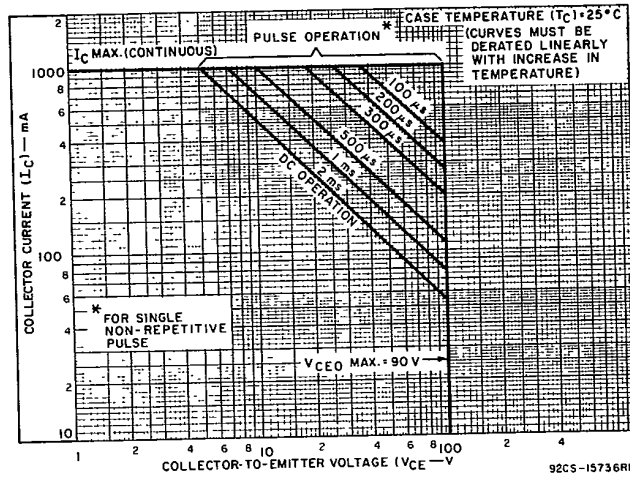


Fig. 1 - Maximum operating areas for type 2N2405.

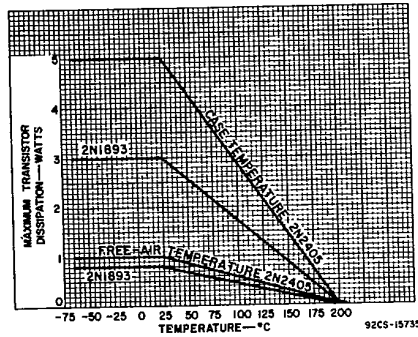


Fig. 2 - Dissipation derating curves for types 2N1893, and 2N2405.

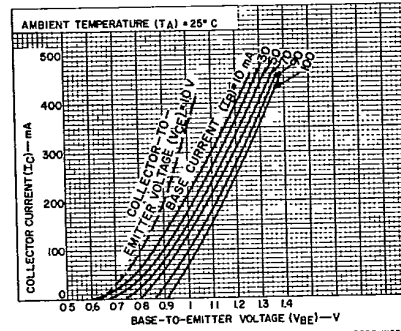


Fig. 3 - Typical transfer characteristics for types 2N1893 and 2N2405.

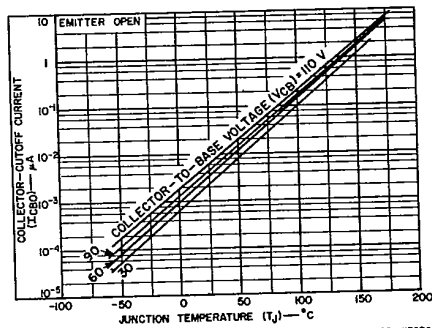


Fig. 4 - Typical cutoff characteristics for types 2N1893 and 2N2405.

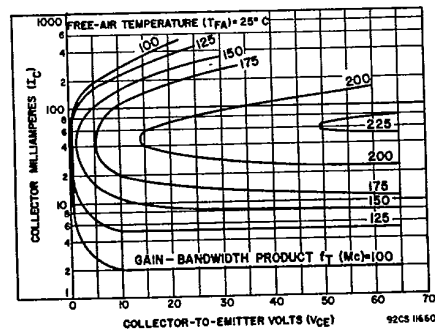


Fig. 5 - Typical gain bandwidth product characteristics for types 2N1893 and 2N2405.

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High-Speed Power Transistors

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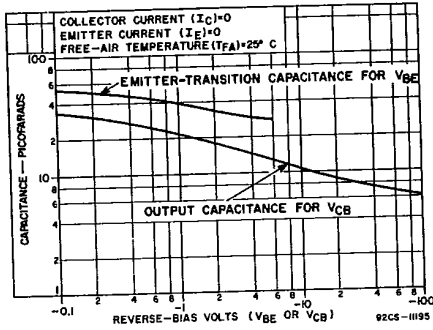


Fig. 6 - Typical capacitance characteristics for types 2N1893 and 2N2405.

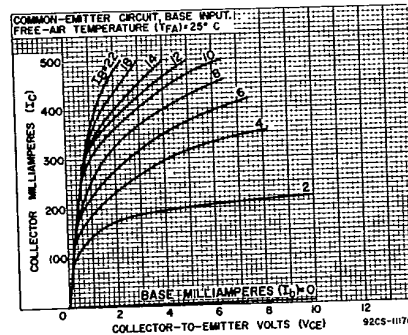


Fig. 7 - Typical collector characteristics at 25°C for type 2N2405.

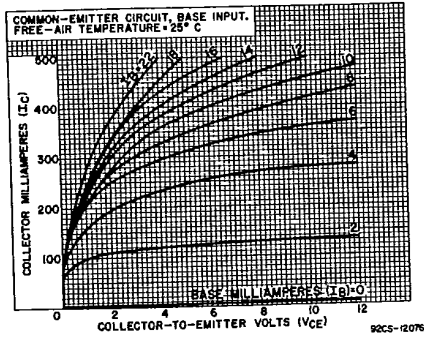


Fig. 8 - Typical collector characteristics at 25°C for type 2N1893.

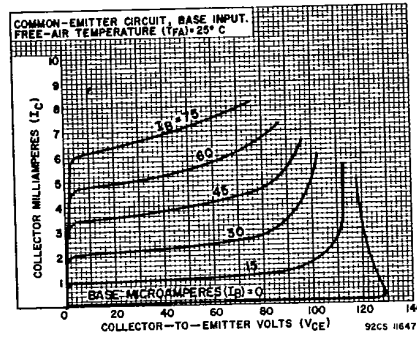


Fig. 9 - Typical collector characteristics at 25°C for type 2N2405.

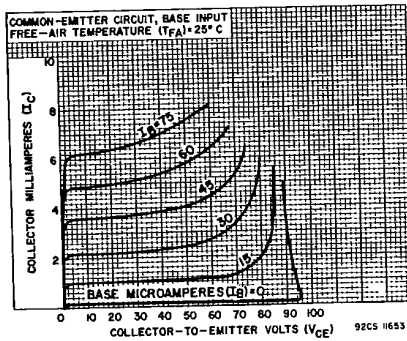


Fig. 10 - Typical collector characteristics at 25°C for type 2N1893.

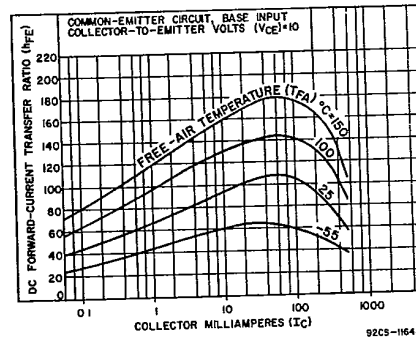


Fig. 11 - Typical dc-beta characteristics for types 2N1893 and 2N2405.

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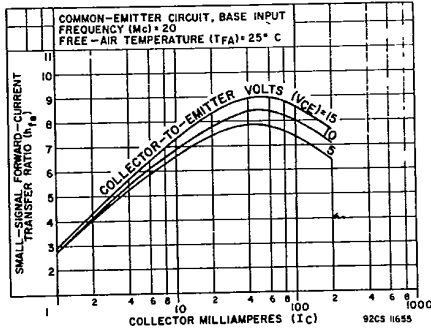


Fig. 12 - Typical small-signal beta characteristics for types 2N1893 and 2N2405.

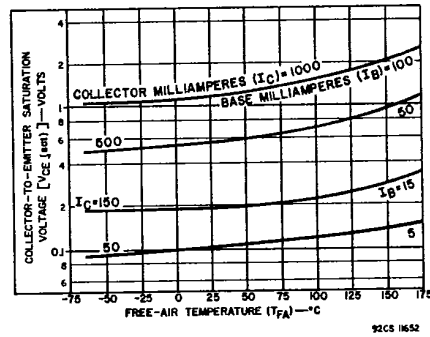


Fig. 13 - Typical saturation characteristics for types 2N1893 and 2N2405.

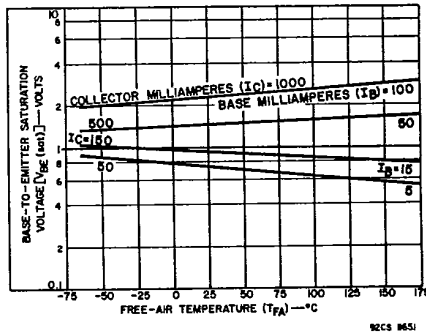


Fig. 14 - Typical saturation characteristics for types 2N2405 and 2N1893.

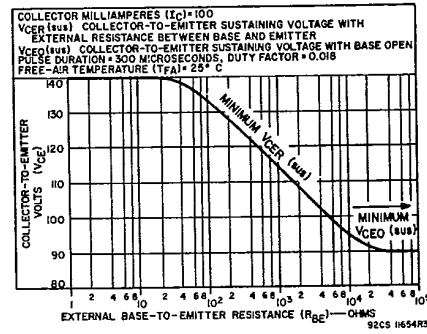


Fig. 15 - Sustaining voltage characteristic for type 2N2405.

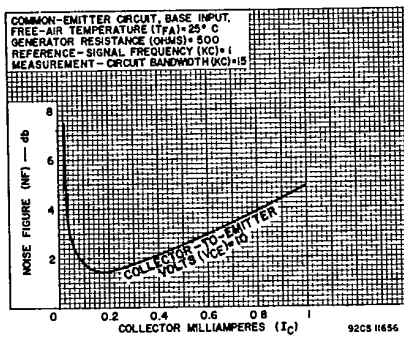


Fig. 16 - Typical wide-band noise characteristic for type 2N2405.

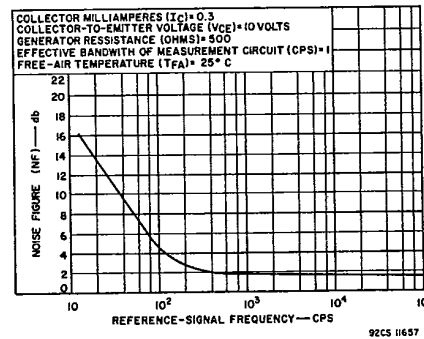


Fig. 17 - Typical narrow-band noise characteristic for type 2N2405.